



# SPN75T10 N-Channel Enhancement Mode MOSFET

## DESCRIPTION

The SPN75T10 is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suitable for synchronous rectifier application, Motor control power management and other Power Tool circuits. It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

## FEATURES

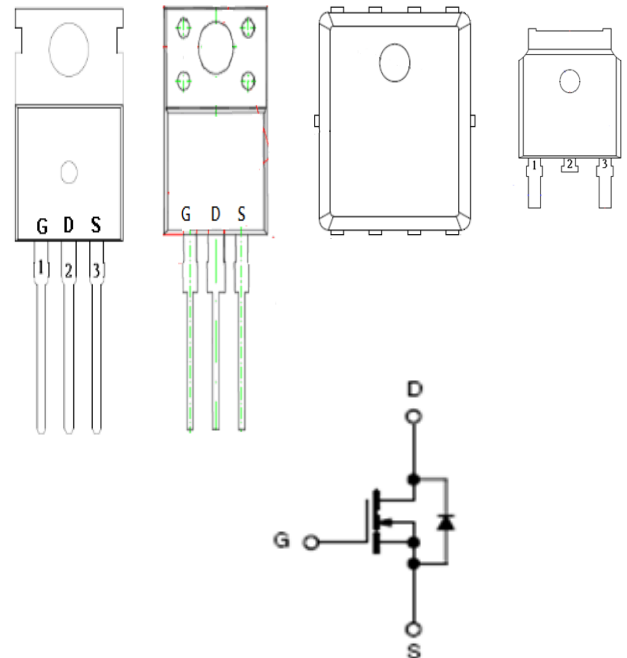
- ◆ 100V/80A,  $R_{DS(ON)}=9.2m\Omega@V_{GS}=10V$
- ◆ 100V/80A,  $R_{DS(ON)}=14m\Omega@V_{GS}=4.5V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TO-220-3L/TO-220F-3L/TO-252-2L/PPAK5x6-8L package design

## APPLICATIONS

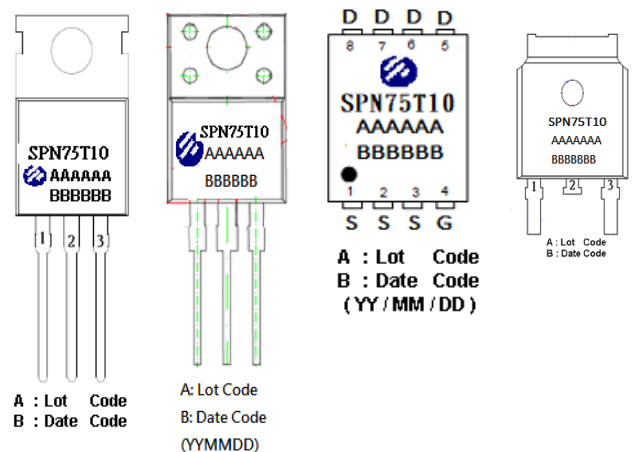
- DC/DC Converter
- Load Switch
- SMPS Secondary Side Synchronous Rectifier
- Power Tool
- Motor Control

## PIN CONFIGURATION

TO-220-3L TO-220F-3L PPAK5x6-8L TO252-2L



## PART MARKING





# SPN75T10

## N-Channel Enhancement Mode MOSFET

### TO-220/TO-220F/TO-252 PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

### PPAK5x6 PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPN75T10T220TGB	TO-220-3L	SPN75T10
SPN75T10T220FTGB	TO-220F-3L	SPN75T10
SPN75T10T252RGB	TO-252-2L	SPN75T10
SPN75T10DN8RGB	PPAK5x6-8L	SPN75T10

- ※ SPN75T10T220TGB : Tube ; Pb – Free ; Halogen – Free
- ※ SPN75T10T220FTGB : Tube ; Pb – Free ; Halogen – Free
- ※ SPN75T10T252RGB : Tape Reel ; Pb – Free ; Halogen – Free
- ※ SPN75T10DN8RGB : Tape Reel ; Pb – Free ; Halogen – Free



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### ABSOLUTE MAXIMUM RATINGS

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Gate –Source Voltage		V <sub>GSS</sub>	+20/-12	V
Continuous Drain Current(Silicon Limited)	T <sub>C</sub> =25°C	I <sub>D</sub>	80	A
	T <sub>C</sub> =100°C		50.6	
Pulsed Drain Current		I <sub>DM</sub>	320	A
Power Dissipation@ T <sub>C</sub> =25°C	TO-220	P <sub>D</sub>	156	W
Power Dissipation@ T <sub>C</sub> =25°C	TO-220F/TO-252		145	
Power Dissipation@ T <sub>C</sub> =25°C	PPAK5x6		135	
Avalanche Energy with Single Pulse ( T <sub>J</sub> =25°C , L=0.1mH , I <sub>AS</sub> =65A , V <sub>DD</sub> =50V , V <sub>GS</sub> =10V)		EAS	211	mJ
Operating Junction Temperature		T <sub>J</sub>	-55/150	°C
Storage Temperature Range		T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient		R <sub>θJA</sub>	62	°C/W
Thermal Resistance-Junction to Case		R <sub>θJC</sub>	0.8	°C/W

#### Note :

The maximum current rating is package limited at 78A for TO-220F-3L

The maximum current rating is package limited at 70A for TO-252-2L

The maximum current rating is package limited at 80A for PPAK5x6-8L



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## N-Channel Enhancement Mode MOSFET

### ELECTRICAL CHARACTERISTICS

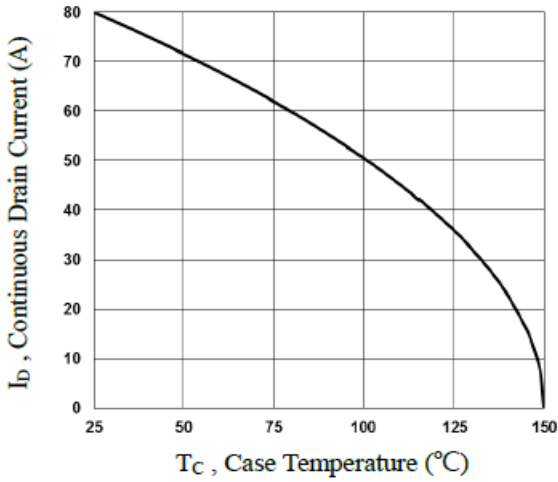
(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.5	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=+20V/-12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V$ $T_J=25^\circ C$			1	uA
		$V_{DS}=80V, V_{GS}=0V$ $T_J=125^\circ C$			10	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=15A$		7.6	9.2	mΩ
		$V_{GS}=4.5V, I_D=8A$		10.8	14	
Diode Forward Voltage	$V_{SD}$	$I_S=1A, V_{GS}=0V, T_J=25^\circ C$			1	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=80V, V_{GS}=10V$ $I_D=8.5A$		39.7	80	nC
Gate-Source Charge	$Q_{gs}$			5.4	10	
Gate-Drain Charge	$Q_{gd}$			11.2	22	
Input Capacitance	$C_{iss}$	$V_{DD}=25V, V_{GS}=0V$ $f=1MHz$		2550	5100	pF
Output Capacitance	$C_{oss}$			685	1370	
Reverse Transfer Capacitance	$C_{rss}$			42	84	
Turn-On Time	$t_{d(on)}$	$V_{DD}=50V,$ $I_D=1A, V_{GS}=10V$ $R_G=6\Omega$		14.6	30	nS
	$t_r$			21.5	44	
Turn-Off Time	$t_{d(off)}$			54	108	
	$t_f$			84.3	168	

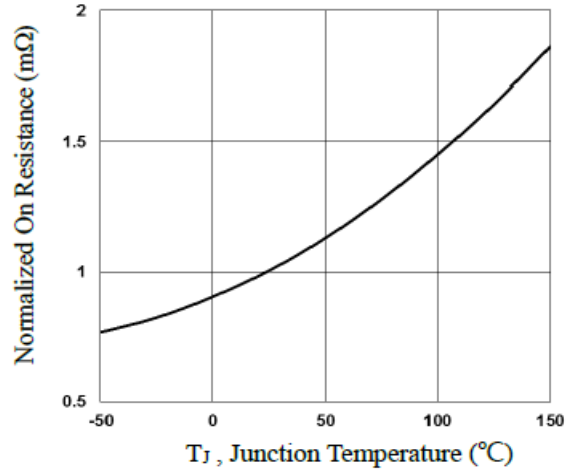


# SPN75T10 N-Channel Enhancement Mode MOSFET

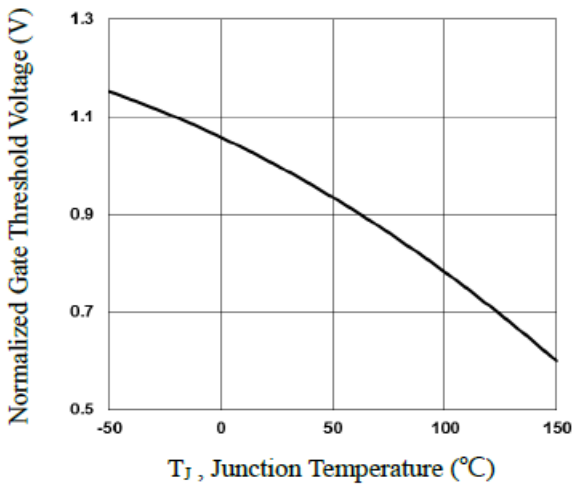
## TYPICAL CHARACTERISTICS



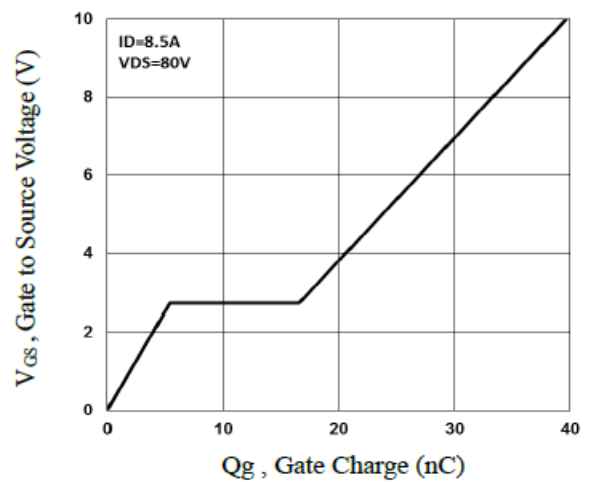
**Fig.1 Continuous Drain Current vs.  $T_C$**



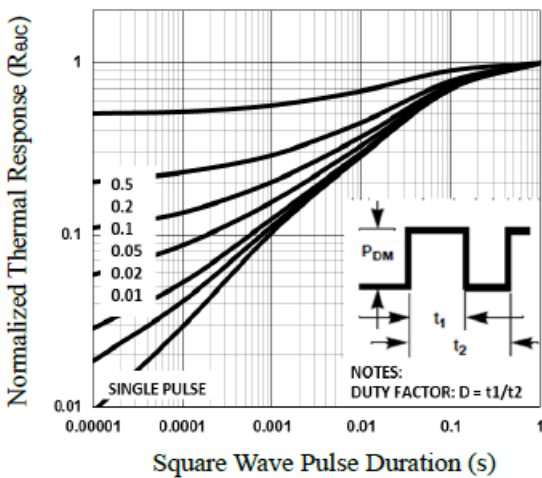
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



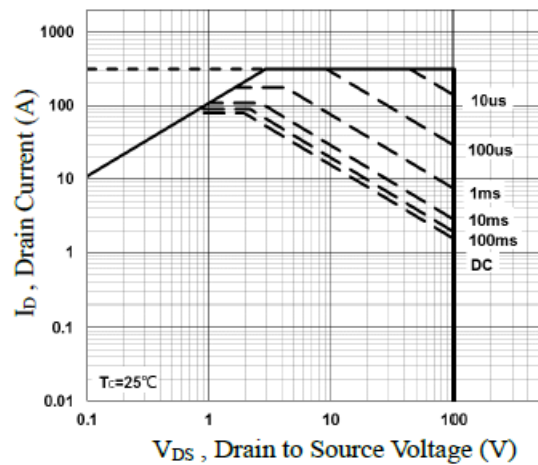
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



**Fig.4 Gate Charge Characteristics**



**Fig.5 Normalized Transient Impedance**

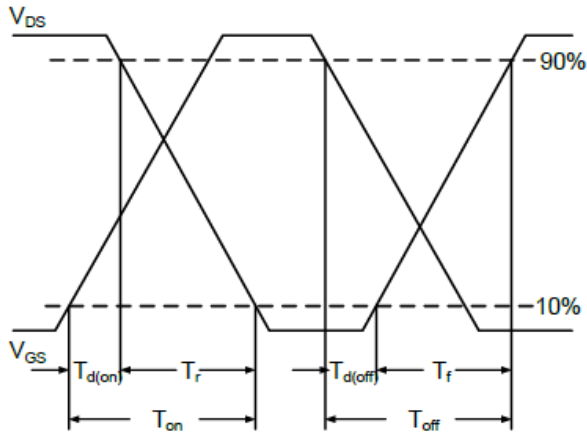


**Fig.6 Maximum Safe Operation Area**

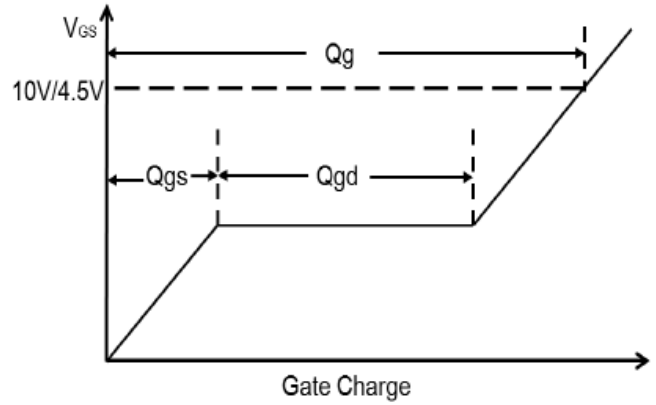


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## TYPICAL CHARACTERISTICS



**Fig.7 Switching Time Waveform**



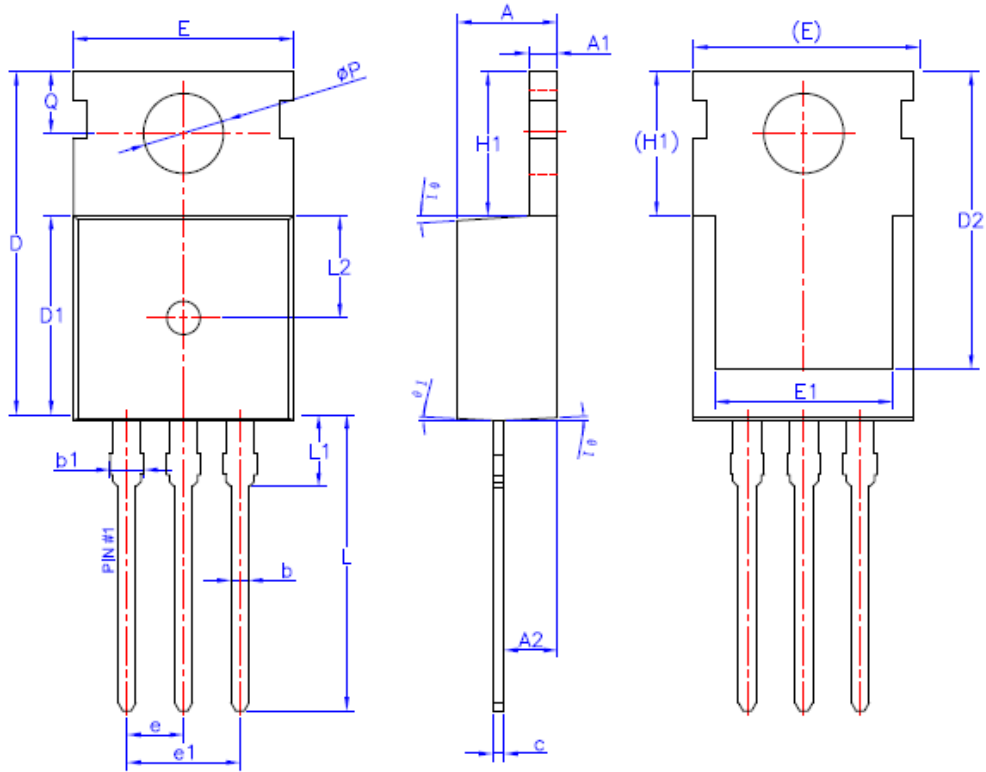
**Fig.8 Gate Charge Waveform**



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## N-Channel Enhancement Mode MOSFET

### TO-220-3L PACKAGE OUTLINE



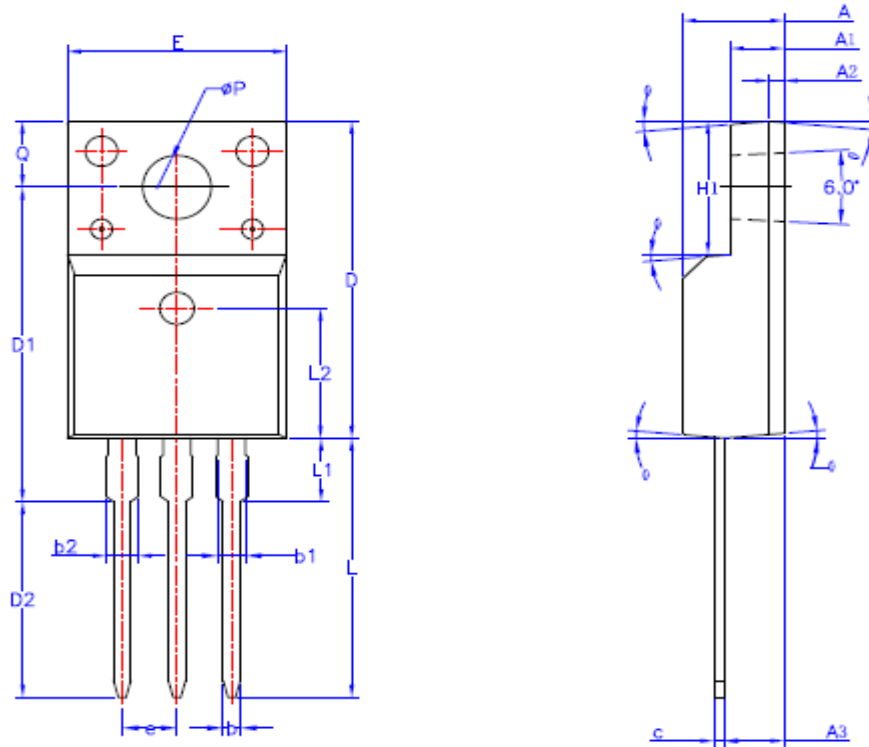
SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	—	0.90
b1	1.42	—	1.57
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	—	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54BSC		
e1	5.08BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	—	—	3.50
L2	4.60REF		
φP	3.55	3.60	3.65
Q	2.73	—	2.87
θ1	1°	3°	5°



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### TO-220F-3L PACKAGE OUTLINE



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.7REF		
A3	2.56	2.76	2.93
b	0.70	--	0.90
b1	1.18	--	1.40
b2	--	--	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.00
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	3.50
L2	6.50REF		
φ P	3.08	3.18	3.28
Q	3.20	-	3.40
θ 1	1°	3°	5°

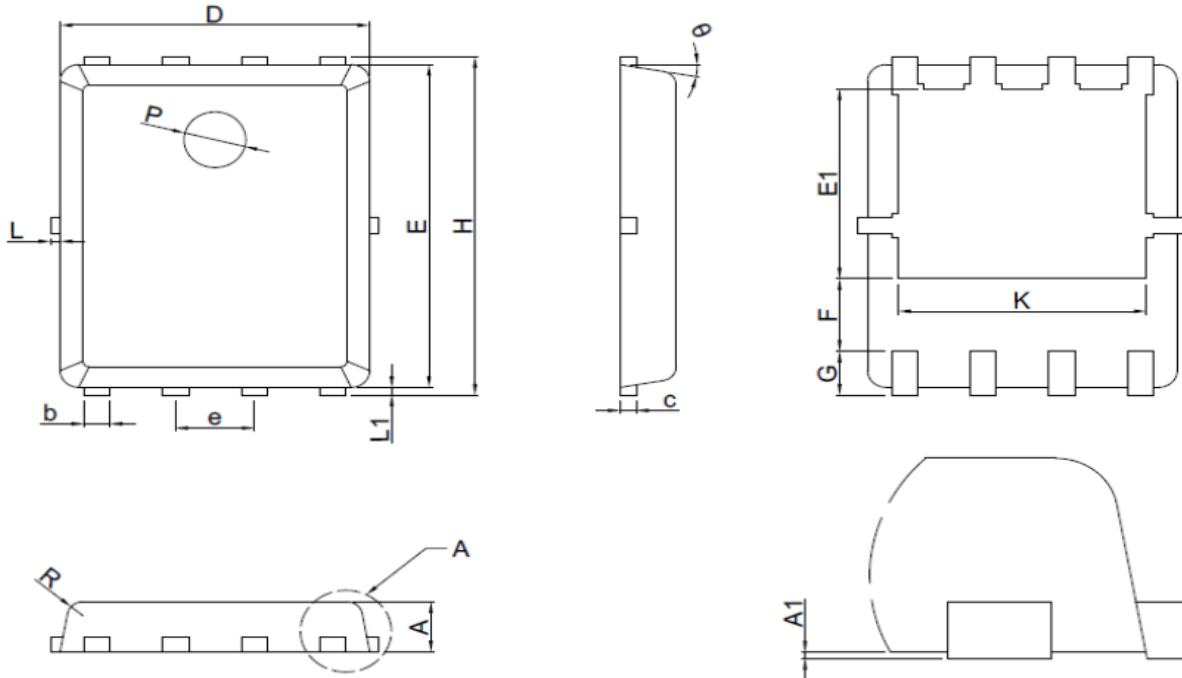




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## N-Channel Enhancement Mode MOSFET

### PPAK5x6-8L PACKAGE OUTLINE



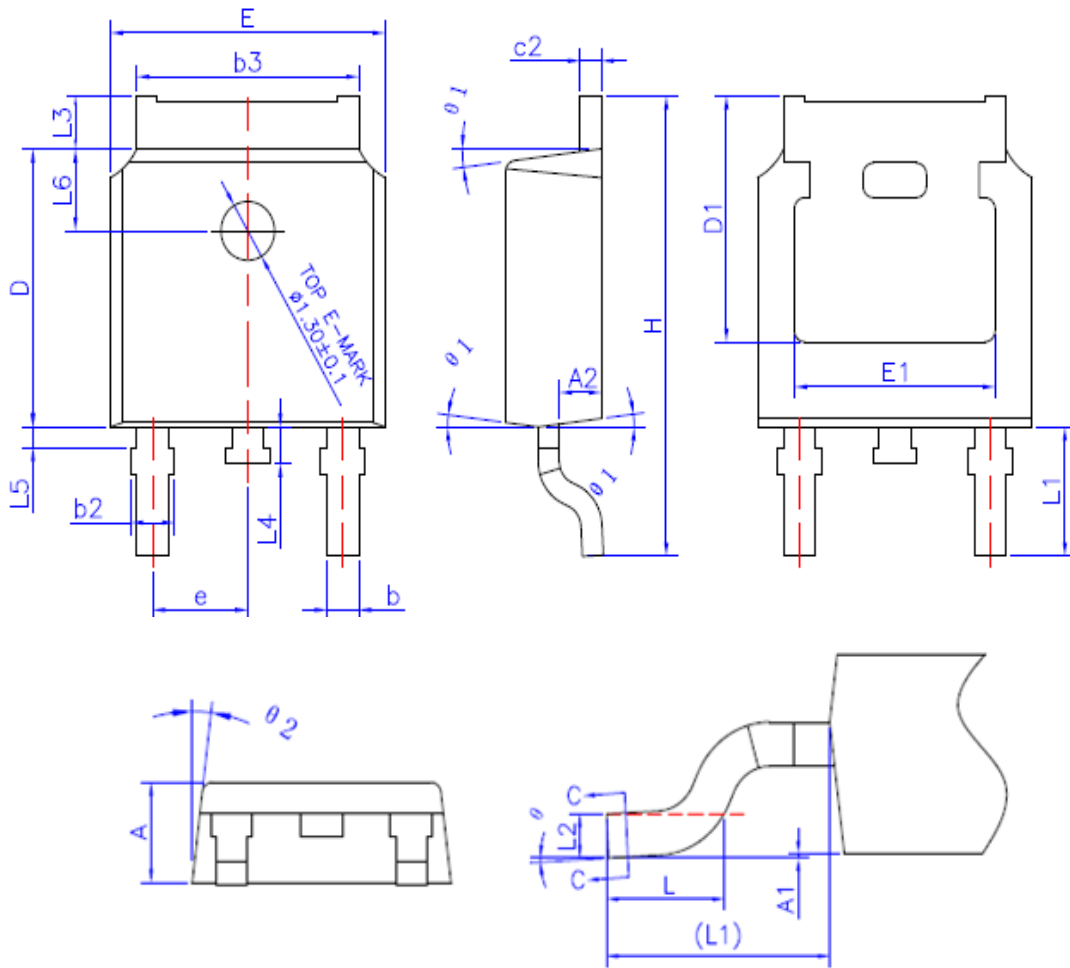
SYMBOL	MILLIMETERS		
	MIN	NOM	MAX
A	0.8	0.95	1.1
A1	0.00	0.03	0.05
b	0.33	0.41	0.51
c	0.254 REF		
D	4.80	4.95	5.10
F	1.40 REF		
E	5.70	5.80	5.90
e	1.27 BSC		
H	5.90	6.05	6.20
L1	0.06	0.13	0.20
G	0.60 REF		
K	4.00 REF		
L	---	---	0.20
P	1.00 REF		
E1	3.40REF		
$\theta$	6°	10°	14°
R	0.25REF		



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## N-Channel Enhancement Mode MOSFET

### TO-252-2L PACKAGE OUTLINE



SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	--	0.15
A2	0.90	1.01	1.10
b	0.72	-	0.85
b2	0.72	--	0.90
b3	5.13	5.33	5.46
c	0.47	--	0.60
c2	0.47	--	0.60
D	6.00	6.10	6.20
D1	5.25	--	--
E	6.40	6.60	6.80
E1	4.70	--	--
e	2.3REF		
H	9.80	10.10	10.40
L	1.40	1.60	1.80
L1	2.90REF		
L2	0.508BSC		
L3	0.90	--	1.25
L4	0.60	0.80	1.00
L5	0.15	--	0.75
L6	1.80REF		
$\theta$	0°	3°	8°
$\theta 1$	5°	7°	9°
$\theta 2$	5°	7°	9°



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